

MITSUBISHI SEMICONDUCTOR <TRANSISTOR ARRAY>

M54519P/FP

7-UNIT 400mA DARLINGTON TRANSISTOR ARRAY

DESCRIPTION

M54519P and M54519FP are seven-circuit Darlington transistor arrays. The circuits are made of NPN transistors. Both the semiconductor integrated circuits perform high-current driving with extremely low input-current supply.

FEATURES

- High breakdown voltage ($BV_{CEO} \geq 40V$)
- High-current driving ($I_c(\max) = 400mA$)
- Driving available with PMOS IC output
- Wide operating temperature range ($T_a = -20$ to $+75^{\circ}C$)

APPLICATION

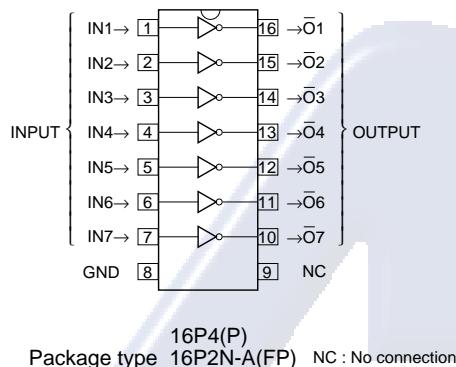
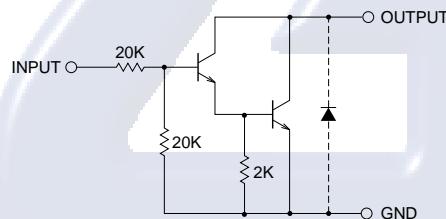
Drives of relays and printers, digit drives of indication elements (LEDs and lamps), and MOS-bipolar logic IC interfaces

FUNCTION

The M54519P and M54519FP each have seven circuits consisting of NPN Darlington transistors. These ICs have resistance of $20k\Omega$ between input transistor bases and input pins. The output transistor emitters are all connected to the GND pin (pin 8).

Collector current is 400mA maximum. Collector-emitter supply voltage is 40V maximum.

The M54519FP is enclosed in a molded small flat package, enabling space-saving design.

PIN CONFIGURATION**CIRCUIT DIAGRAM**

The seven circuits share the GND.
The diode, indicated with the dotted line, is parasitic, and cannot be used.

Unit : Ω **ABSOLUTE MAXIMUM RATINGS** (Unless otherwise noted, $T_a = -20$ ~ $+75^{\circ}C$)

Symbol	Parameter	Conditions	Ratings	Unit
V_{CEO}	Collector-emitter voltage	Output, H	-0.5 ~ +40	V
I_c	Collector current	Current per circuit output, L	400	mA
V_I	Input voltage		-0.5 ~ +40	V
P_d	Power dissipation	$T_a = 25^{\circ}C$, when mounted on board	1.47(P)/1.00(FP)	W
T_{opr}	Operating temperature		-20 ~ +75	$^{\circ}C$
T_{stg}	Storage temperature		-55 ~ +125	$^{\circ}C$

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RECOMMENDED OPERATING CONDITIONS (Unless otherwise noted, Ta = -20 ~ +75°C)

Symbol	Parameter	Limits			Unit
		min	typ	max	
Vo	Output voltage	0	—	40	V
Ic	Collector current (Current per 1 circuit when 7 circuits are coming on simultaneously)	Duty Cycle P : no more than 8% FP : no more than 6%	0	—	400 mA
		Duty Cycle P : no more than 30% FP : no more than 25%	0	—	200 mA
VIH	"H" input voltage	Ic ≤ 400mA	8	—	V
		Ic ≤ 200mA	5	—	
VIL	"L" input voltage	0	—	0.5	V

ELECTRICAL CHARACTERISTICS (Unless otherwise noted, Ta = -20 ~ +75°C)

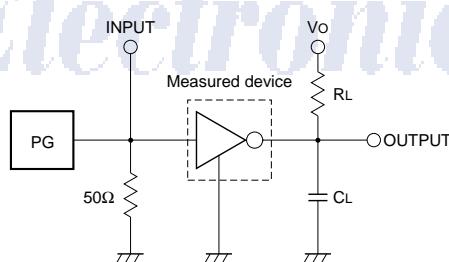
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ*	max	
V (BR) CEO	Collector-emitter breakdown voltage	ICEO = 100µA	40	—	—	V
VCE (sat)	Collector-emitter saturation voltage	VI = 8V, IC = 400mA	—	1.3	2.4	V
		VI = 5V, IC = 200mA	—	1.0	1.6	
II	Input current	VI = 17V	0.3	0.8	1.8	mA
hFE	DC amplification factor	VCE = 4V, IC = 400mA, Ta = 25°C	1000	6000	—	—

* : The typical values are those measured under ambient temperature (Ta) of 25°C. There is no guarantee that these values are obtained under any conditions.

SWITCHING CHARACTERISTICS (Unless otherwise noted, Ta = 25°C)

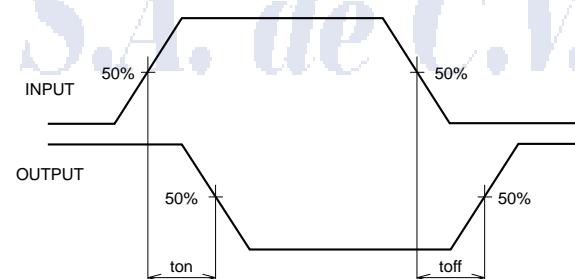
Symbol	Parameter	Test conditions	Limits			Unit
			min	typ	max	
ton	Turn-on time	CL = 15pF (note 1)	—	40	—	ns
toff	Turn-off time		—	400	—	ns

NOTE 1 TEST CIRCUIT



- (1) Pulse generator (PG) characteristics : PRR = 1kHz, tw = 10µs, tr = 6ns, tf = 6ns, ZO = 50Ω, VP = 8Vp-p
- (2) Input-output conditions : RL = 25Ω, Vo = 10V
- (3) Electrostatic capacity CL includes floating capacitance at connections and input capacitance at probes

TIMING DIAGRAM



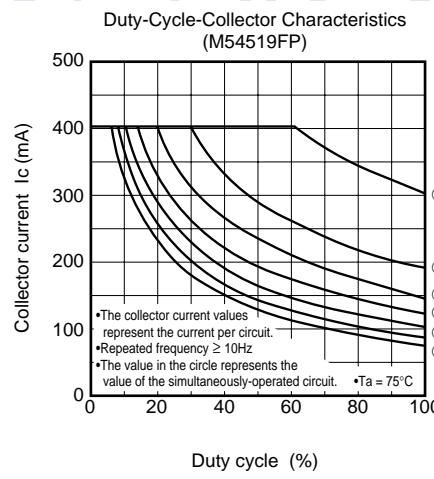
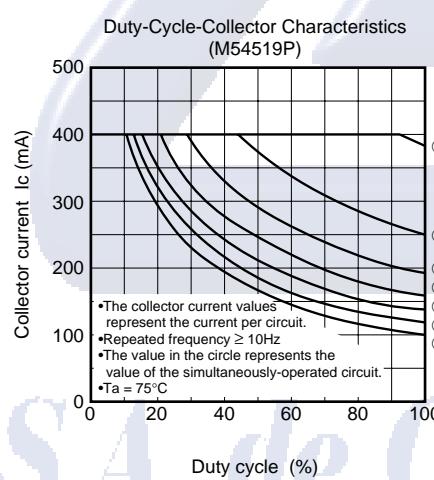
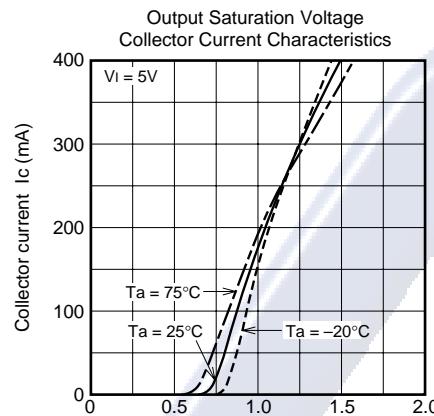
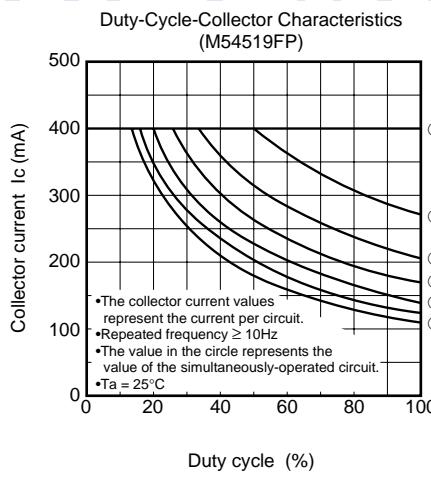
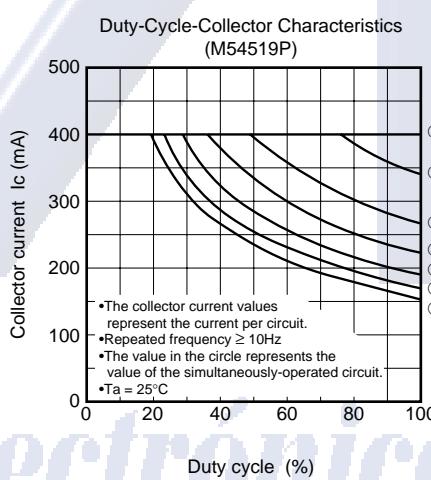
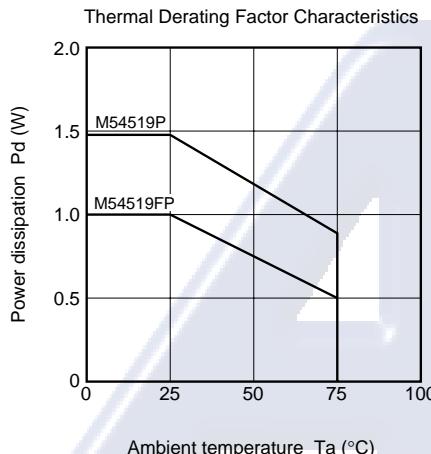
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TYPICAL CHARACTERISTICS

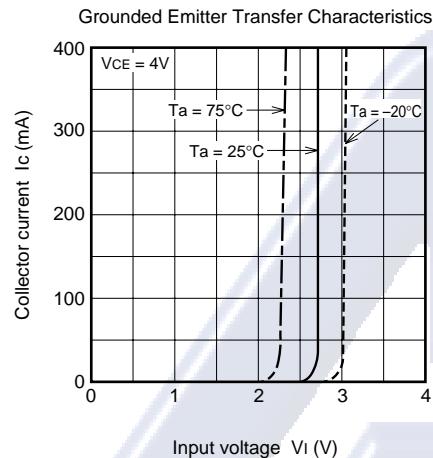
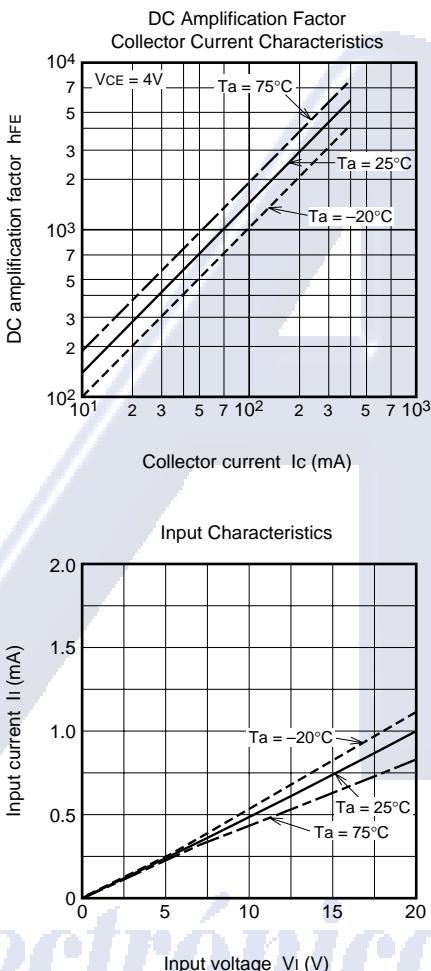


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Electrónica S.A. de C.V.

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